IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-21 (Cancelled)

22. (Currently amended) A method of spin-coating a semiconductor substrate, comprising the steps of:

(a) dropping coating material onto a semiconductor substrate;

(b) rotating said semiconductor substrate about a center thereof; and

(c) generating an electric field circumferentially around said semiconductor substrate and said coating material, said electric field having an electric polarity opposite to an electric polarity of said coating material, wherein said electric field is generated by at least one electrode positioned circumferentially around said semiconductor substrate and wherein said at least one electrode is rotatable about said center of said semiconductor substrate separately from rotation of said semiconductor substrate.

23. (Original) The method as set forth in claim 22, further comprising the step of locally varying an intensity of said electric field circumferentially of said semiconductor substrate.

24. (Original) The method as set forth in claim 23, wherein an intensity of said electric field is varied in regions of said semiconductor substrate circumferentially facing each other.

25. (Original) The method as set forth in claim 22, further comprising the step of locally varying an intensity of said electric field vertically of said semiconductor substrate.

26. (Original) The method as set forth in claim 22, further comprising the step of varying an intensity of said electric field periodically with lapse of time.

27. (Original) The method as set forth in claim 22, further comprising the step of generating a second electric field below said semiconductor substrate by a voltage having an electric polarity opposite to an electric polarity of said coating material.

28. (Original) The method as set forth in claim 22, wherein a force applied to said coating material by said electric field is almost equal to a gravitational force exerted on said coating material.